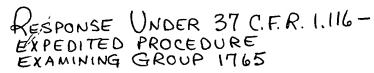
DOCKET NO. 99-039



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DEC 1 9 2002

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants;

Sheldon Aronowitz, Valeriy Sukharev, John Haywood, James P. Kimball, Helmut Puchner, Ravindra Manohar Kapre, and Nicholas Eib

Appl. No.

09/464,297

Filed:

December 15, 1999

Title

PROCESS FOR ETCHING A CONTROLLABLE THICKNESS OF

OXIDE ON AN INTEGRATED CIRCUIT STRUCTURE ON A SEMICONDUCTOR SUBSTRATE USING NITROGEN PLASMA AND

AN RF BIAS APPLIED TO THE SUBSTRATE

Grp./ A.U.

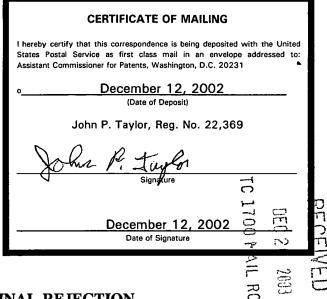
1765

Examiner

Charlotte A. Brown

Docket No.

99-039



RESPONSE TO FINAL REJECTION

Honorable Commissioner for Patents Washington, D.C. 20231

Date: December 12, 2002

Sir:

The following remarks are in response to the second Final Rejection mailed October 24, 2002, in this application.